



No.4634

2SK1839
N-Channel Enhancement MOS Silicon FET
Analog Switch Applications

Features

- Very small-sized package permitting 2SK1839-applied sets to be made small and slim.
- Large $|Y_{fs}|$.
- Enhancement type.
- Low ON resistance.

Absolute Maximum Ratings at Ta = 25°C

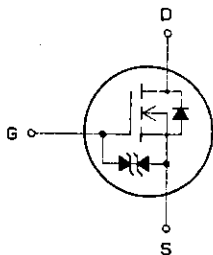
			unit
Drain-to-Source Voltage	V_{DSS}	30	V
Gate-to-Source Voltage	V_{GSS}	± 12	V
Drain Current(DC)	I_D	100	mA
Drain Current(Pulse)	I_{DP}	300	mA
Allowable Power Dissipation	P_D	150	mW
Channel Temperature	T_{ch}	125	°C
Storage Temperature	T_{stg}	-55 to +125	°C

Electrical Characteristics at Ta = 25°C

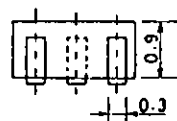
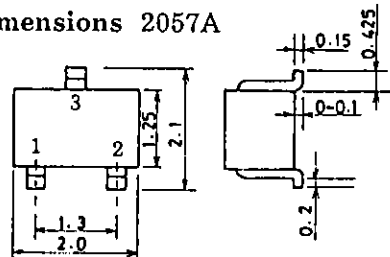
			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 10\mu A, V_{GS} = 0$	30			V
Drain Current	I_{DSS}	$V_{DS} = 15V, V_{GS} = 0$			1	μA
Gate Cutoff Current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0$		0.01	± 10	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 100\mu A$	0.3	0.9	1.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, I_D = 50mA, f = 1kHz$	25	50		mS
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10mA$		15	25	Ω
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		12		pF
Output Capacitance	C_{oss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		4		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		0.4		pF

Marking : JJ

Electrical Connection

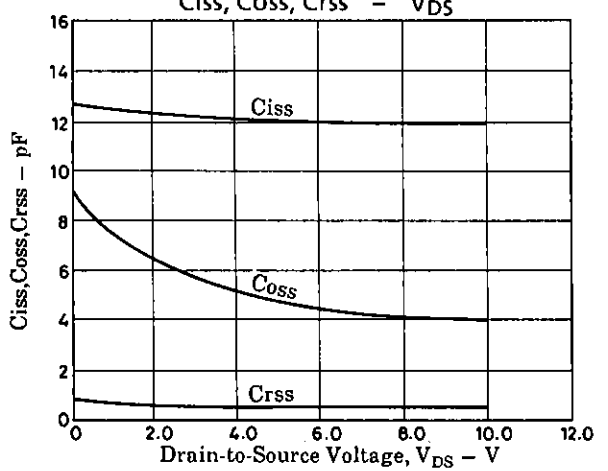
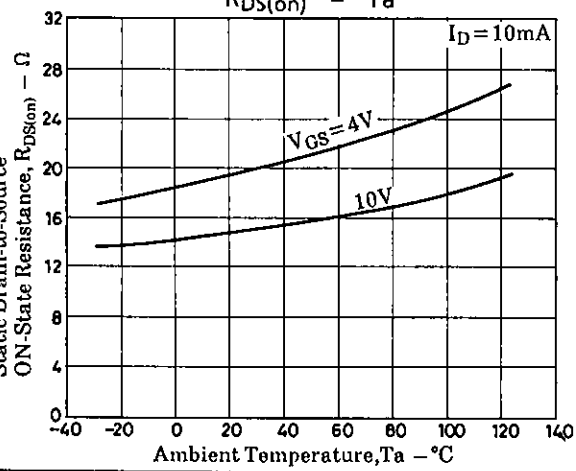
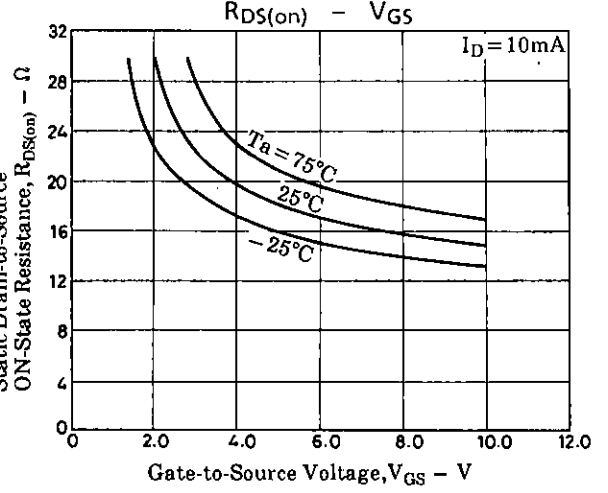
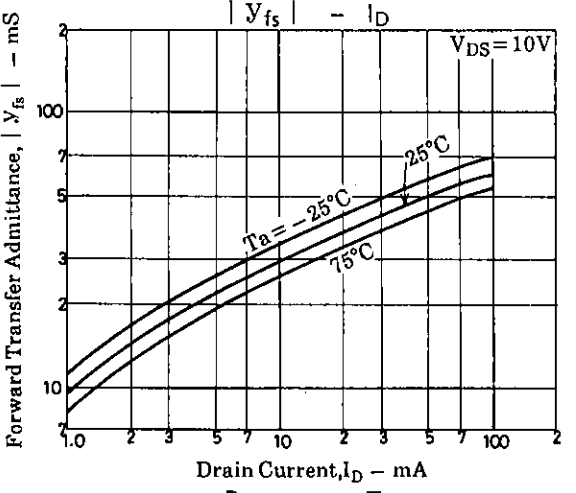
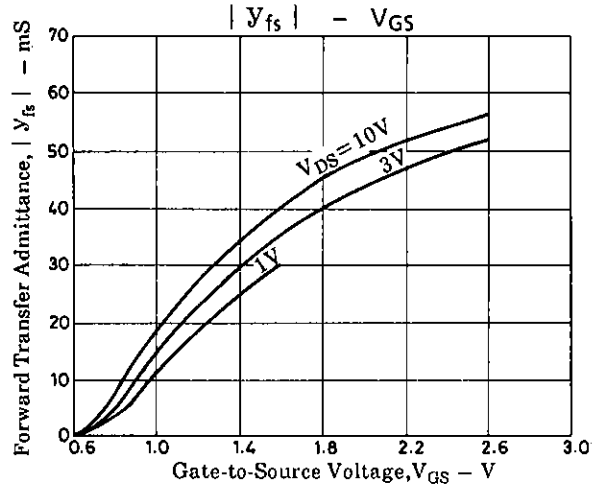
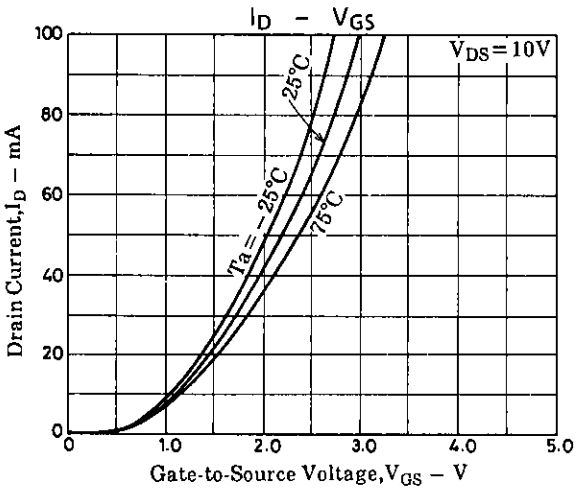
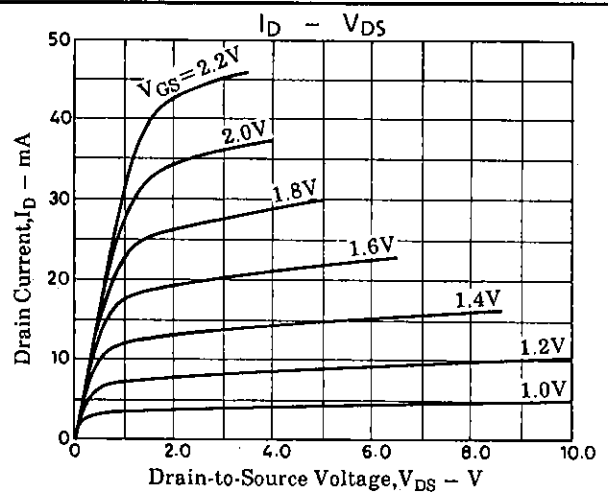
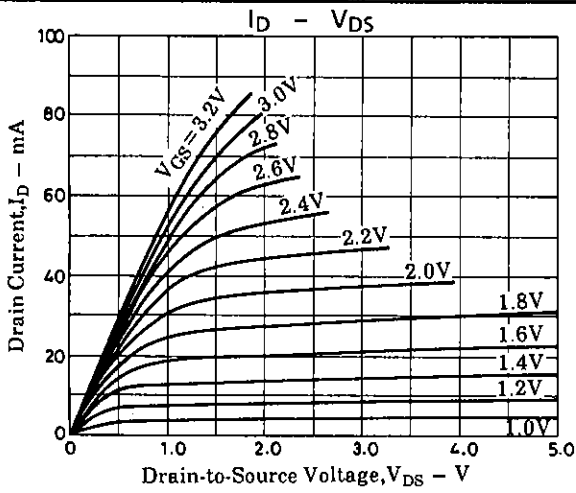


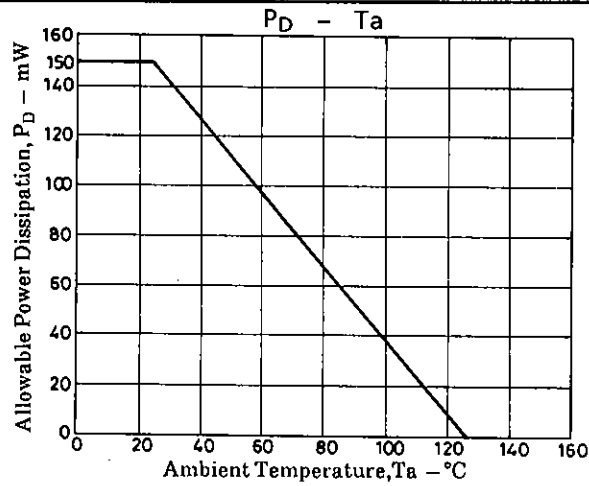
Package Dimensions 2057A
(unit : mm)



1 : Gate
2 : Drain
3 : Source

SANYO : MCP





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